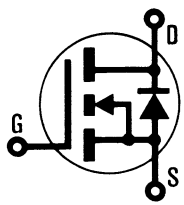
INTERNATIONAL RECTIFIER IOR

HEXFET® TRANSISTORS

N-CHANNEL POWER MOSFETs



IRFJ120
IRFJ121
IRFJ122
IRFJ123

100 Volt, 0.3 Ohm HEXFET

The HEXFET® technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry and unique processing of the HEXFET design achieve very low on-state resistance combined with high transconductance and great device ruggedness.

The HEXFET transistors also feature all of the well established advantages of MOSFETs such as voltage control, freedom from second breakdown, very fast switching, ease of paralleling, and temperature stability of the electrical parameters.

They are well suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, and high energy pulse circuits.

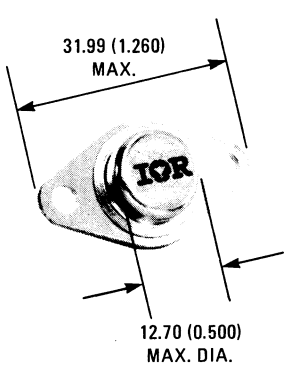
Features:

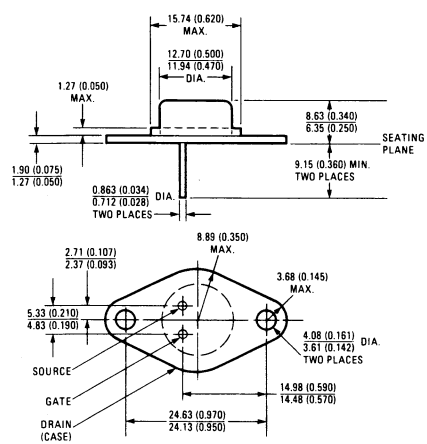
- Fast Switching
- Low Drive Current
- Ease of Paralleling
- No Second Breakdown
- Excellent Temperature Stability

Product Summary

Part Number	V_{DS}	$R_{DS(on)}$	I_D
IRFJ120	100V	0.3Ω	8.0A
IRFJ121	60V	0.3Ω	8.0A
IRFJ122	100V	0.4Ω	7.0A
IRFJ123	60V	0.4Ω	7.0A

CASE STYLE AND DIMENSIONS





Conforms to JEDEC Case Style TO-213AA (TO-66)
Dimensions in Millimeters and (Inches)

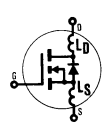
Absolute Maximum Ratings

Parameter		IRFJ120	IRFJ121	IRFJ122	IRFJ123	Units
V_{DS}	Drain - Source Voltage ①	100	60	100	60	V
V_{DGR}	Drain - Gate Voltage (R_{GS} = 20 KΩ) ①	100	60	100	60	V
I_D @ T_C = 25°C	Continuous Drain Current	8.0	8.0	7.0	7.0	A
I_D @ T_C = 100°C	Continuous Drain Current	5.0	5.0	4.0	4.0	A
I_{DM}	Pulsed Drain Current ③	32	32	28	28	A
V_{GS}	Gate - Source Voltage	±20				V
P_D @ T_C = 25°C	Max. Power Dissipation	40 (See Fig. 14)				W
	Linear Derating Factor	0.32 (See Fig. 14)				W/K
I_{LM}	Inductive Current, Clamped	(See Fig. 15 and 16) L = 100μH				A
		32	32	28	28	
T_J T_{stg}	Operating Junction and Storage Temperature Range	-55 to 150				°C
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)				°C

Electrical Characteristics @T_C = 25°C (Unless Otherwise Specified)

Parameter		Type	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain - Source Breakdown Voltage	IRFJ120 IRFJ122	100	–	–	V	V_{GS} = 0V
		IRFJ121 IRFJ123	60	–	–	V	I_D = 250μA
$V_{GS(th)}$	Gate Threshold Voltage	ALL	2.0	–	4.0	V	V_{DS} = V_{GS}, I_D = 250μA
I_{GSS}	Gate - Source Leakage Forward	ALL	–	–	100	nA	V_{GS} = 20V
I_{GSS}	Gate - Source Leakage Reverse	ALL	–	–	-100	nA	V_{GS} = -20V
I_{DSS}	Zero Gate Voltage Drain Current	ALL	–	–	250	μA	V_{DS} = Max. Rating, V_{GS} = 0V
			–	–	1000	μA	V_{DS} = Max. Rating x 0.8, V_{GS} = 0V, T_C = 125°C
$I_{D(on)}$	On-State Drain Current ②	IRFJ120 IRFJ121	8.0	–	–	A	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max.}$, V_{GS} = 10V
		IRFJ122 IRFJ123	7.0	–	–	A	
$R_{DS(on)}$	Static Drain-Source On-State Resistance ②	IRFJ120 IRFJ121	–	0.25	0.30	Ω	V_{GS} = 10V, I_D = 4.0A
		IRFJ122 IRFJ123	–	0.30	0.40	Ω	
g_{fs}	Forward Transconductance ②	ALL	1.5	2.9	–	S (℧)	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max.}$, I_D = 4.0A
C_{iss}	Input Capacitance	ALL	–	450	600	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1.0 MHz See Fig. 10
C_{oss}	Output Capacitance	ALL	–	200	400	pF	
C_{rss}	Reverse Transfer Capacitance	ALL	–	50	100	pF	
$t_{d(on)}$	Turn-On Delay Time	ALL	–	20	40	ns	V_{DD} ≅ 0.5 BV_{DSS}, I_D = 4.0A, Z_o = 50Ω See Fig. 17 (MOSFET switching times are essentially independent of operating temperature.)
t_r	Rise Time	ALL	–	35	70	ns	
$t_{d(off)}$	Turn-Off Delay Time	ALL	–	50	100	ns	
t_f	Fall Time	ALL	–	35	70	ns	
Q_g	Total Gate Charge (Gate-Source Plus Gate-Drain)	ALL	–	10	15	nC	V_{GS} = 10V, I_D = 10A, V_{DS} = 0.8 Max. Rating. See Fig. 18 for test circuit. (Gate charge is essentially independent of operating temperature.)
Q_{gs}	Gate-Source Charge	ALL	–	6.0	–	nC	
Q_{gd}	Gate-Drain ("Miller") Charge	ALL	–	4.0	–	nC	
L_D	Internal Drain Inductance	ALL	–	5.0	–	nH	Measured between the contact screw on header that is closer to source and gate pins and center of die.
L_S	Internal Source Inductance	ALL	–	12.5	–	nH	Measured from the source pin, 6 mm (0.25 in.) from header and source bonding pad.

Modified MOSFET symbol showing the internal device inductances.



Thermal Resistance

R_{thJC}	Junction-to-Case	ALL	–	–	3.1	K/W	
R_{thCS}	Case-to-Sink	ALL	–	0.2	–	K/W	Mounting surface flat, smooth, and greased.
R_{thJA}	Junction-to-Ambient	ALL	–	–	50	K/W	Free Air Operation

Source-Drain Diode Ratings and Characteristics

I_S	Continuous Source Current (Body Diode)	IRFJ120 IRFJ121	–	–	8.0	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier.
		IRFJ122 IRFJ123	–	–	7.0	A	
I_{SM}	Pulse Source Current (Body Diode)③	IRFJ120 IRFJ121	–	–	32	A	
		IRFJ122 IRFJ123	–	–	28	A	
V_{SD}	Diode Forward Voltage ②	IRFJ120 IRFJ121	–	–	2.5	V	T_C = 25°C, I_S = 8.0A, V_{GS} = 0V
		IRFJ122 IRFJ123	–	–	2.3	V	T_C = 25°C, I_S = 7.0A, V_{GS} = 0V
t_{rr}	Reverse Recovery Time	ALL	–	280	–	ns	T_J = 150°C, I_F = 8.0A, dI_F/dt = 100A/μs
Q_{RR}	Reverse Recovered Charge	ALL	–	1.6	–	μC	T_J = 150°C, I_F = 8.0A, dI_F/dt = 100A/μs
t_{on}	Forward Turn-on Time	ALL	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				

①T_J = 25°C to 150°C. ②Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%. ③Repetitive Rating: Pulse width limited by max. junction temperature. See Transient Thermal Impedance Curve (Fig. 5).

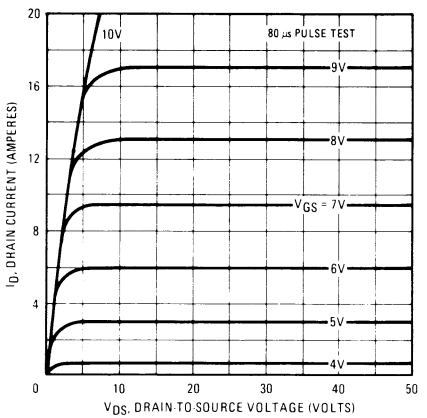


Fig. 1 – Typical Output Characteristics

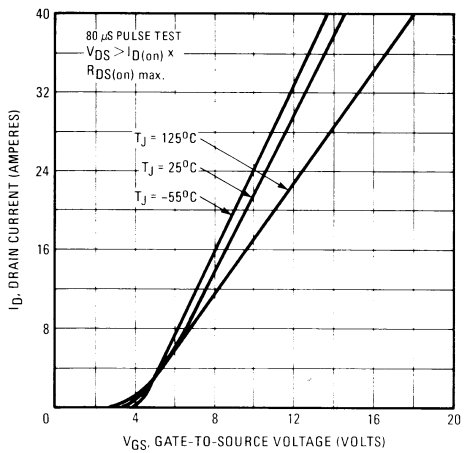


Fig. 2 – Typical Transfer Characteristics

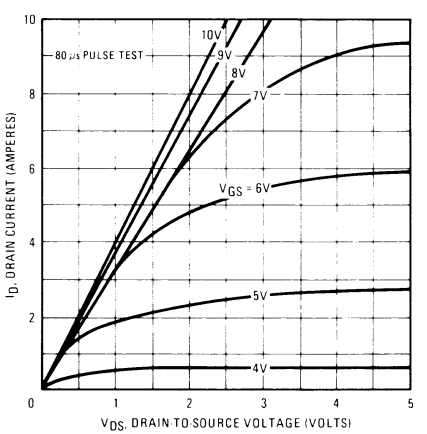


Fig. 3 – Typical Saturation Characteristics

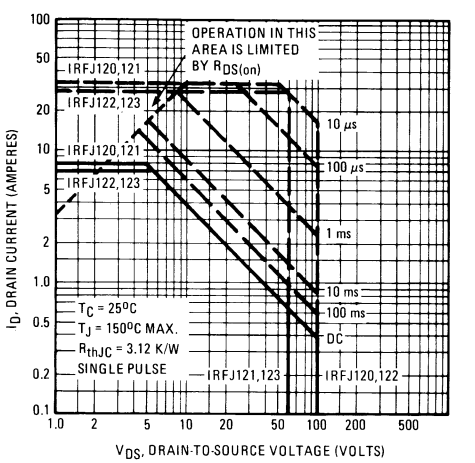


Fig. 4 – Maximum Safe Operating Area

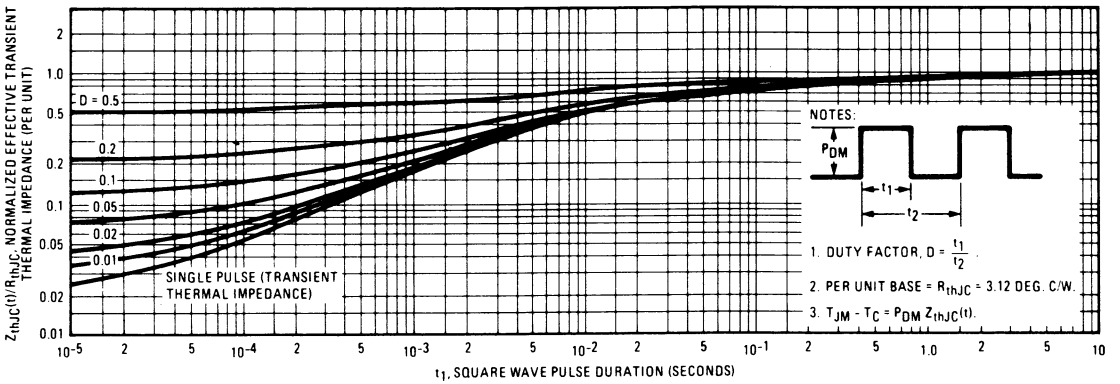


Fig. 5 – Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

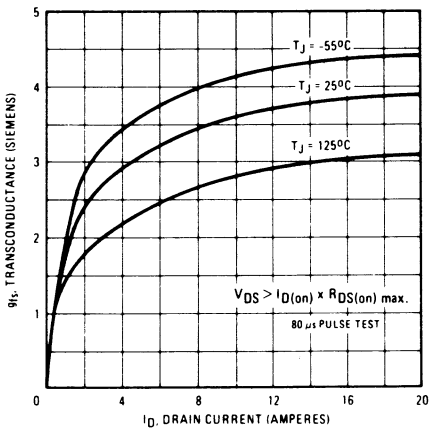


Fig. 6 – Typical Transconductance Vs. Drain Current

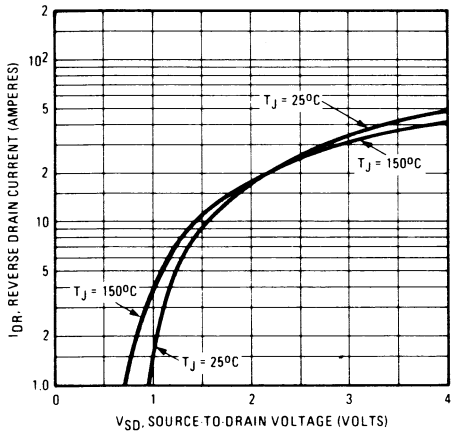


Fig. 7 – Typical Source-Drain Diode Forward Voltage

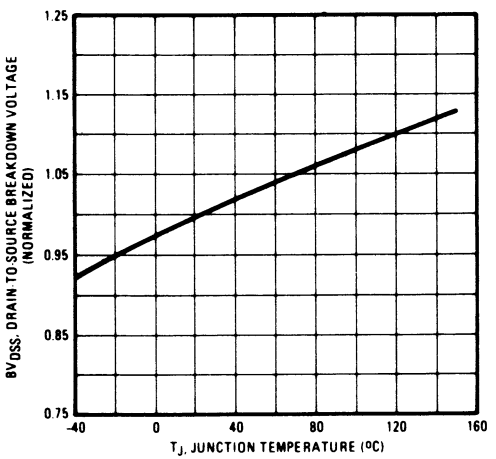


Fig. 8 – Breakdown Voltage Vs. Temperature

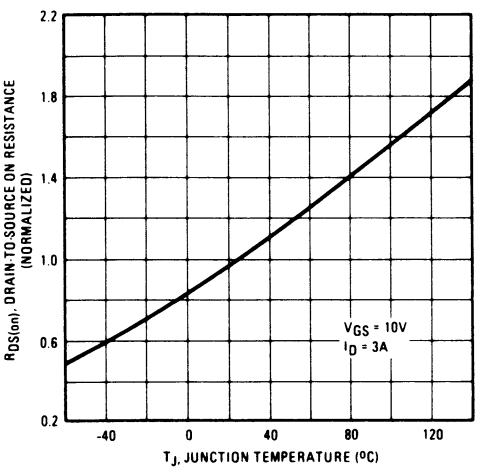


Fig. 9 – Normalized On-Resistance Vs. Temperature

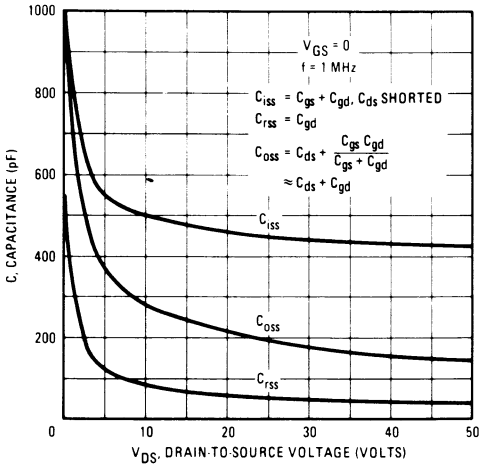


Fig. 10 – Typical Capacitance Vs. Drain-to-Source Voltage

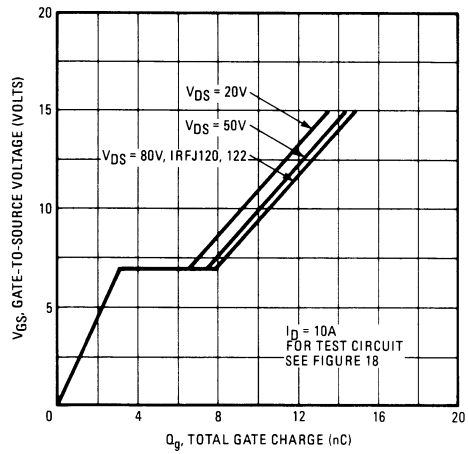


Fig. 11 – Typical Gate Charge Vs. Gate-to-Source Voltage

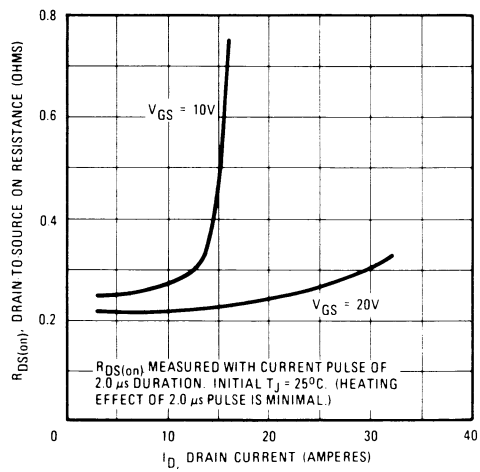


Fig. 12 – Typical On-Resistance Vs. Drain Current

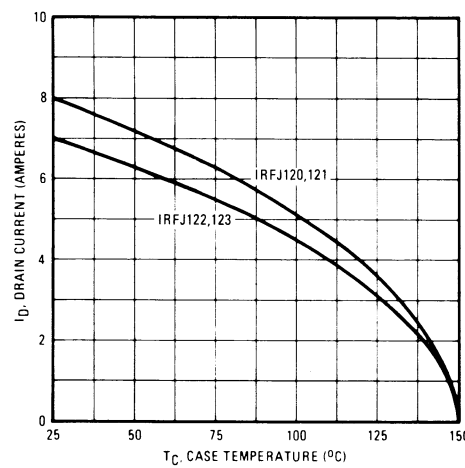


Fig. 13 – Maximum Drain Current Vs. Case Temperature

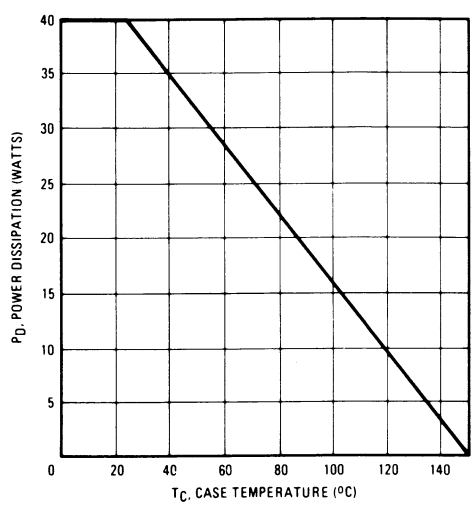


Fig. 14 – Power Vs. Temperature Derating Curve

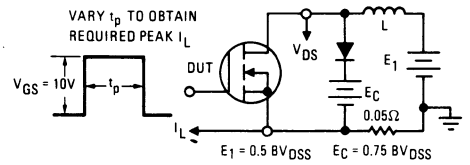


Fig. 15 – Clamped Inductive Test Circuit

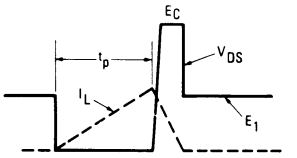


Fig. 16 – Clamped Inductive Waveforms

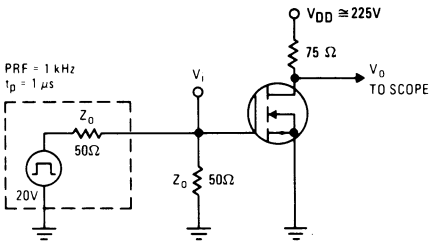


Fig. 17 – Switching Time Test Circuit

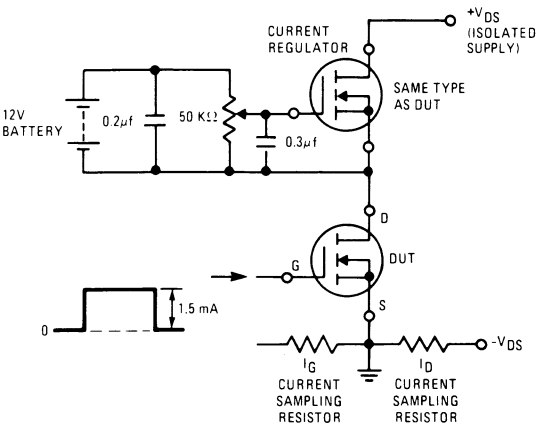


Fig. 18 – Gate Charge Test Circuit

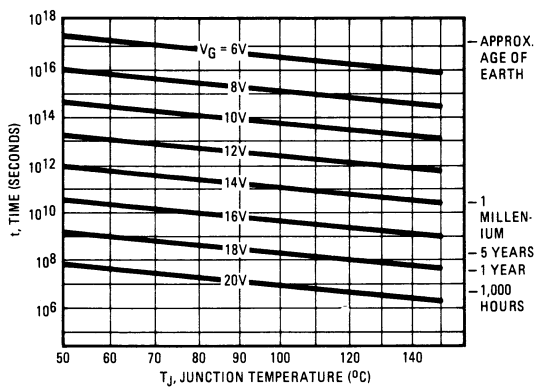


*Fig. 19 – Typical Time to Accumulated 1% Failure

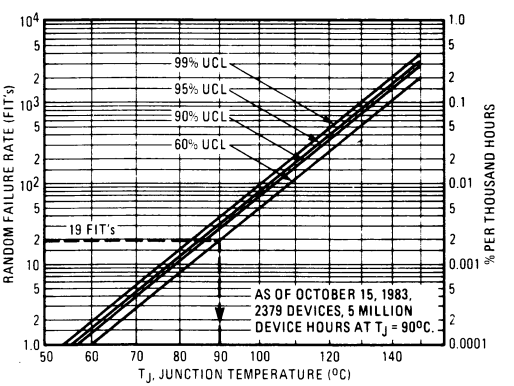


Fig. 20 – Typical High Temperature Reverse Bias (HTRB) Failure Rate

*The data shown is correct as of April 15, 1984. This information is updated on a quarterly basis; for the latest reliability data, please contact your local IR field office.

Data Sheet No. PD-9.398

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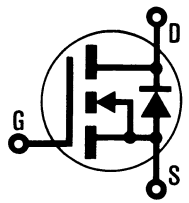
N-CHANNEL POWER MOSFETs



IRFJ130
IRFJ131
IRFJ132
IRFJ133

100 Volt, 0.18 Ohm HEXFET

The HEXFET® technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry and unique processing of the HEXFET design achieve very low on-state resistance combined with high transconductance and great device ruggedness.

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They are well suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, and high energy pulse circuits.

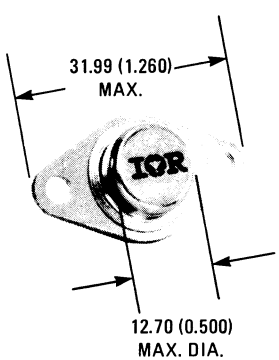
Features:

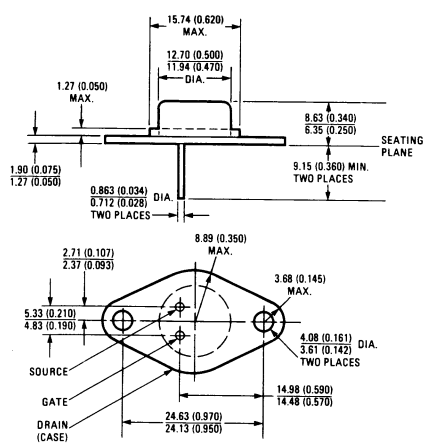
- Fast Switching
- Low Drive Current
- Ease of Paralleling
- No Second Breakdown
- Excellent Temperature Stability

Product Summary

Part Number	V_{DS}	$R_{DS(on)}$	I_D
IRFJ130	100V	0,18Ω	10A
IRFJ131	60V	0.18Ω	10A
IRFJ132	100V	0.25Ω	10A
IRFJ133	60V	0.25Ω	10A

CASE STYLE AND DIMENSIONS





Conforms to JEDEC Case Style TO-213AA (TO-66)
Dimensions in Millimeters and (Inches)

IRFJ130, IRFJ131, IRFJ132, IRFJ133 Devices

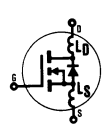
Absolute Maximum Ratings

Parameter		IRFJ130	IRFJ131	IRFJ132	IRFJ133	Units
V_{DS}	Drain - Source Voltage ①	100	60	100	60	V
V_{DGR}	Drain - Gate Voltage (R_{GS} = 20 kΩ) ①	100	60	100	60	V
I_D @ T_C = 25°C	Continuous Drain Current *	10	10	10	10	A
I_D @ T_C = 100°C	Continuous Drain Current	7.5	7.5	6.0	6.0	A
I_{DM}	Pulsed Drain Current ③	40	40	40	40	A
V_{GS}	Gate - Source Voltage	± 20				V
P_D @ T_C = 25°C	Max. Power Dissipation	50 (See Fig. 14)				W
	Linear Derating Factor	0.40 (See Fig. 14)				W/K
I_{LM}	Inductive Current, Clamped	(See Fig. 15 and 16) L = 100μH				A
		40	40	40	40	
T_J T_{stg}	Operating Junction and Storage Temperature Range	-55 to 150				°C
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)				°C

Electrical Characteristics @T_C = 25°C (Unless Otherwise Specified)

Parameter		Type	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain - Source Breakdown Voltage	IRFJ130 IRFJ132	100	–	–	V	V_{GS} = 0V
		IRFJ131 IRFJ133	60	–	–	V	I_D = 250μA
$V_{GS(th)}$	Gate Threshold Voltage	ALL	2.0	–	4.0	V	V_{DS} = V_{GS}, I_D = 250μA
I_{GSS}	Gate - Source Leakage Forward	ALL	–	–	100	nA	V_{GS} = 20V
I_{GSS}	Gate - Source Leakage Reverse	ALL	–	–	-100	nA	V_{GS} = -20V
I_{DSS}	Zero Gate Voltage Drain Current	ALL	–	–	250	μA	V_{DS} = Max. Rating, V_{GS} = 0V
			–	–	1000	μA	V_{DS} = Max. Rating x 0.8, V_{GS} = 0V, T_C = 125°C
$I_{D(on)}$	On-State Drain Current ②	IRFJ130 IRFJ131	10	–	–	A	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max.}$, V_{GS} = 10V
		IRFJ132 IRFJ133	10	–	–	A	
$R_{DS(on)}$	Static Drain-Source On-State Resistance ②	IRFJ130 IRFJ131	–	0.14	0.18	Ω	V_{GS} = 10V, I_D = 6.0A
		IRFJ132 IRFJ133	–	0.20	0.25	Ω	
g_{fs}	Forward Transconductance ②	ALL	4.0	5.5	–	S (℧)	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max.}$, I_D = 6.0A
C_{iss}	Input Capacitance	ALL	–	600	800	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1.0 MHz See Fig. 10
C_{oss}	Output Capacitance	ALL	–	300	500	pF	
C_{rss}	Reverse Transfer Capacitance	ALL	–	100	150	pF	
$t_{d(on)}$	Turn-On Delay Time	ALL	–	–	30	ns	V_{DD} ≃ 36V, I_D = 6.0A, Z_o = 15Ω See Fig. 17 (MOSFET switching times are essentially independent of operating temperature.)
t_r	Rise Time	ALL	–	–	75	ns	
$t_{d(off)}$	Turn-Off Delay Time	ALL	–	–	40	ns	
t_f	Fall Time	ALL	–	–	45	ns	
Q_g	Total Gate Charge (Gate-Source Plus Gate-Drain)	ALL	–	18	30	nC	V_{GS} = 10V, I_D = 15A, V_{DS} = 0.8 Max. Rating. See Fig. 18 for test circuit. (Gate charge is essentially independent of operating temperature.)
Q_{gs}	Gate-Source Charge	ALL	–	9.0	–	nC	
Q_{gd}	Gate-Drain (''Miller'') Charge	ALL	–	9.0	–	nC	
L_D	Internal Drain Inductance	ALL	–	5.0	–	nH	Measured between the contact screw on header that is closer to source and gate pins and center of die.
L_S	Internal Source Inductance	ALL	–	12.5	–	nH	Measured from the source pin, 6 mm (0.25 in.) from header and source bonding pad.

Modified MOSFET symbol showing the internal device inductances.



Thermal Resistance

R_{thJC}	Junction-to-Case	ALL	–	–	2.5	K/W	
R_{thCS}	Case-to-Sink	ALL	–	0.2	–	K/W	Mounting surface flat, smooth, and greased.
R_{thJA}	Junction-to-Ambient	ALL	–	–	50	K/W	Free Air Operation

*I_D Limited by pin dimension

Source-Drain Diode Ratings and Characteristics

I_S	Continuous Source Current (Body Diode)	IRFJ130 IRFJ131	–	–	10	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier.
		IRFJ132 IRFJ133	–	–	10	A	
I_{SM}	Pulse Source Current (Body Diode) ③	IRFJ130 IRFJ131	–	–	40	A	
		IRFJ132 IRFJ133	–	–	40	A	
V_{SD}	Diode Forward Voltage ②	IRFJ130 IRFJ131	–	–	2.5	V	T_C = 25°C, I_S = 10A, V_{GS} = 0V
		IRFJ132 IRFJ133	–	–	2.3	V	T_C = 25°C, I_S = 10A, V_{GS} = 0V
t_{rr}	Reverse Recovery Time	ALL	–	360	–	ns	T_J = 150°C, I_F = 10A, dI_F/dt = 100A/μs
Q_{RR}	Reverse Recovered Charge	ALL	–	2.1	–	μC	T_J = 150°C, I_F = 10A, dI_F/dt = 100A/μs
t_{on}	Forward Turn-on Time	ALL	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				

①T_J = 25°C to 150°C. ②Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%. ③Repetitive Rating: Pulse width limited by max. junction temperature. See Transient Thermal Impedance Curve (Fig. 5).

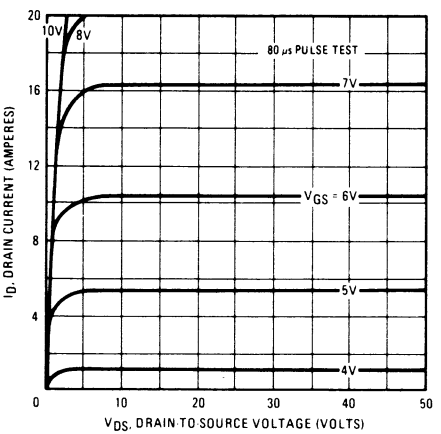


Fig. 1 — Typical Output Characteristics

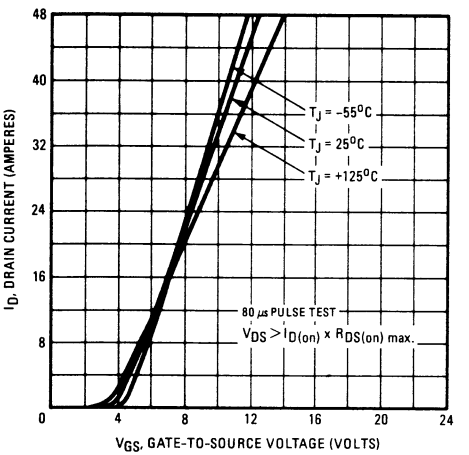


Fig. 2 — Typical Transfer Characteristics

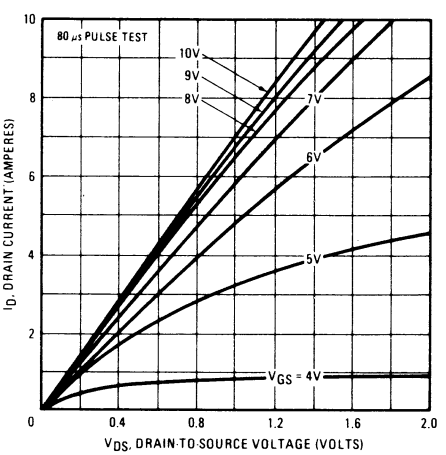


Fig. 3 — Typical Saturation Characteristics

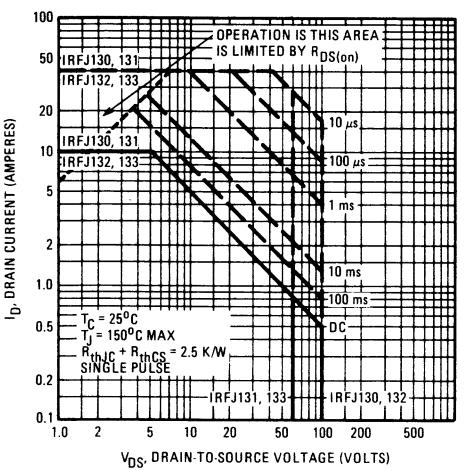


Fig. 4 — Maximum Safe Operating Area

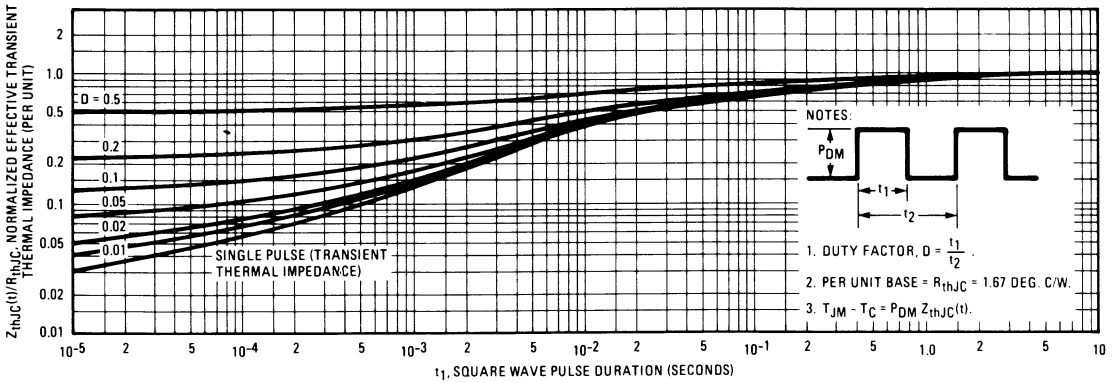


Fig. 5 – Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

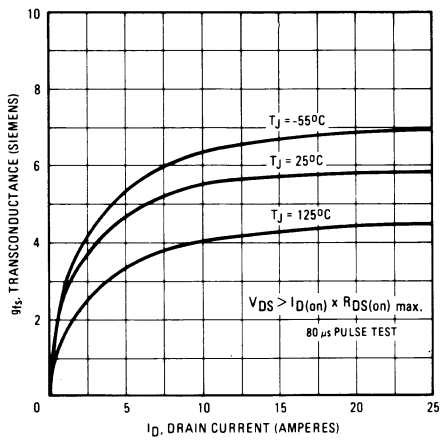


Fig. 6 – Typical Transconductance Vs. Drain Current

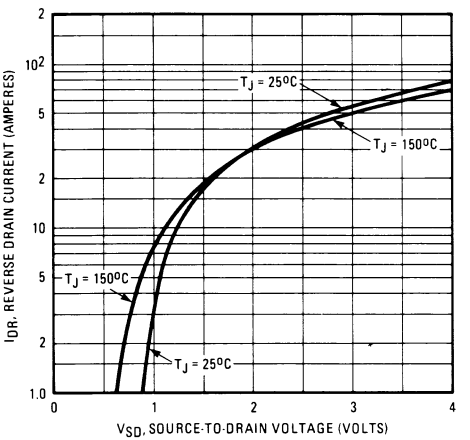


Fig. 7 – Typical Source-Drain Diode Forward Voltage

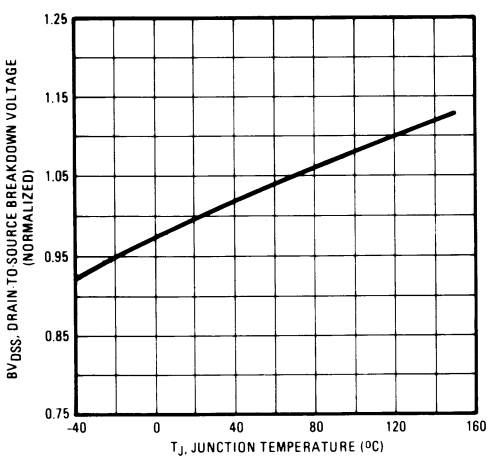


Fig. 8 – Breakdown Voltage Vs. Temperature

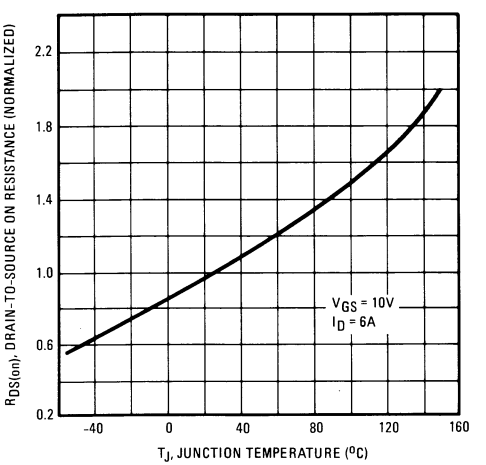


Fig. 9 – Normalized On-Resistance Vs. Temperature

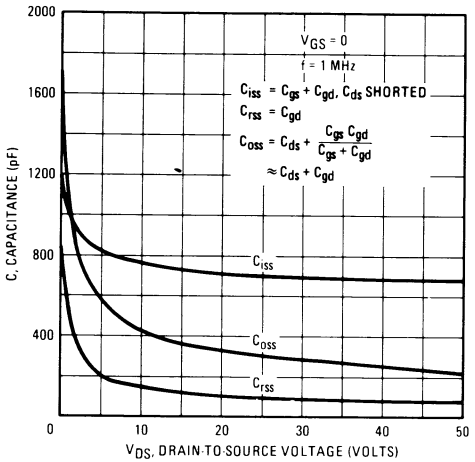


Fig. 10 — Typical Capacitance Vs. Drain-to-Source Voltage

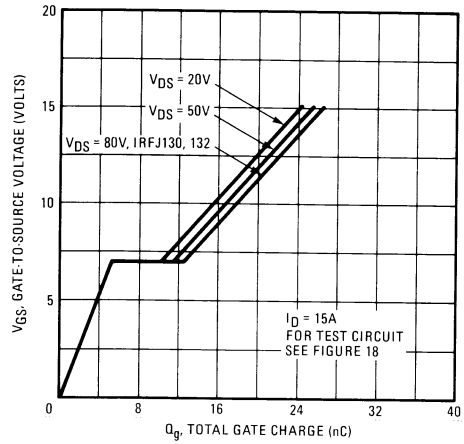


Fig. 11 — Typical Gate Charge Vs. Gate-to-Source Voltage

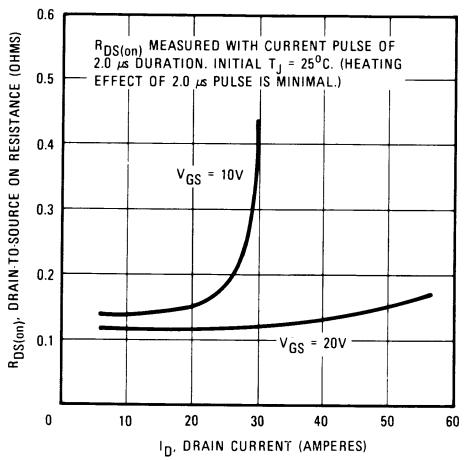


Fig. 12 — Typical On-Resistance Vs. Drain Current

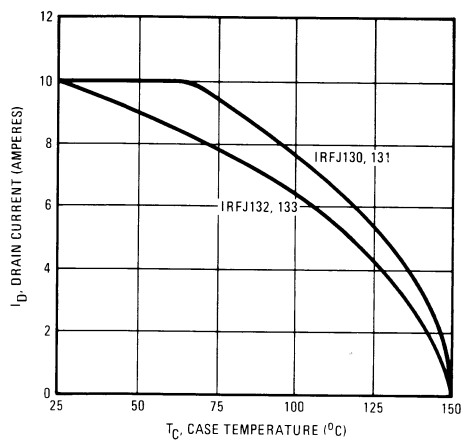


Fig. 13 — Maximum Drain Current Vs. Case Temperature

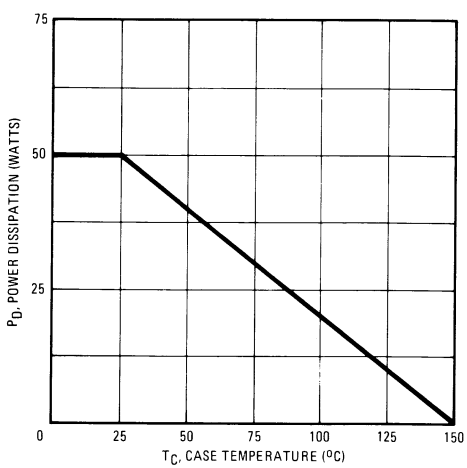


Fig. 14 — Power Vs. Temperature Derating Curve

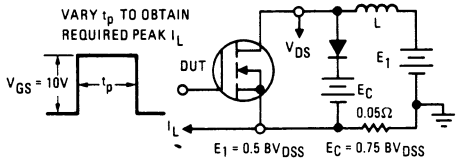


Fig. 15 – Clamped Inductive Test Circuit

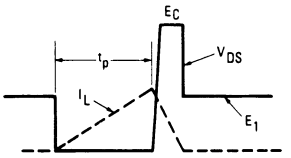


Fig. 16 – Clamped Inductive Waveforms

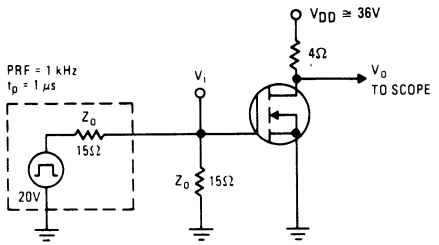


Fig. 17 – Switching Time Test Circuit

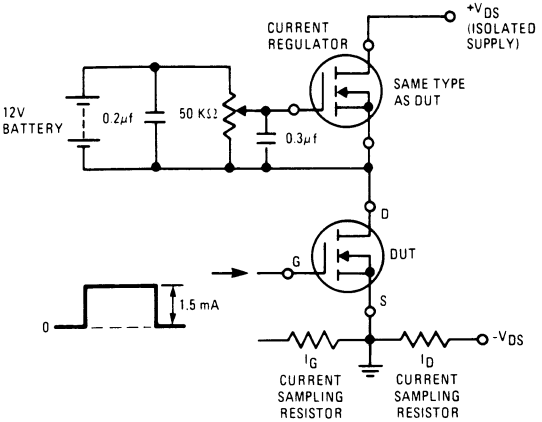
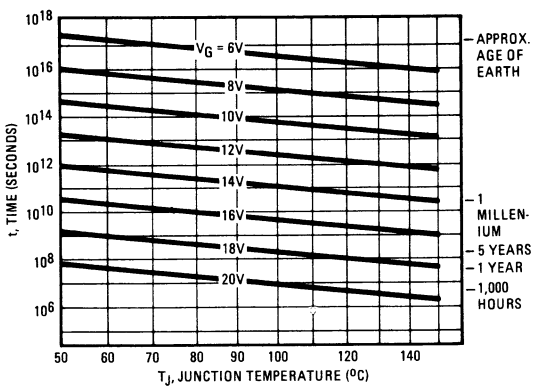


Fig. 18 – Gate Charge Test Circuit



* Fig. 19 – Typical Time to Accumulated 1% Failure

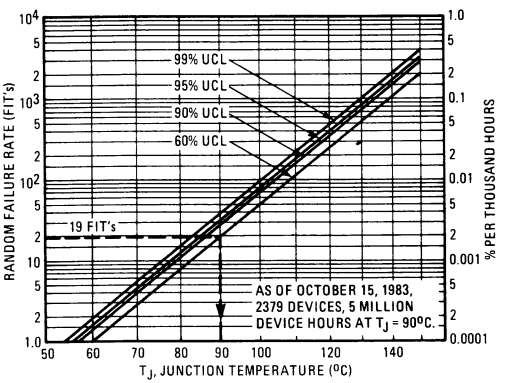


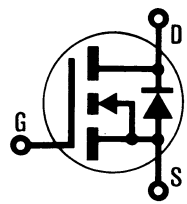
Fig. 20 – Typical High Temperature Reverse Bias (HTRB) Failure Rate

*The data shown is correct as of April 15, 1984. This information is updated on a quarterly basis; for the latest reliability data, please contact your local IR field office.

INTERNATIONAL RECTIFIER IOR

HEXFET® TRANSISTORS

N-CHANNEL POWER MOSFETs



IRFJ140
IRFJ141
IRFJ142
IRFJ143

100 Volt, 0.085 Ohm HEXFET

The HEXFET® technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry and unique processing of the HEXFET design achieve very low on-state resistance combined with high transconductance and great device ruggedness.

The HEXFET transistors also feature all of the well established advantages of MOSFETs such as voltage control, freedom from second breakdown, very fast switching, ease of paralleling, and temperature stability of the electrical parameters.

They are well suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers, and high energy pulse circuits.

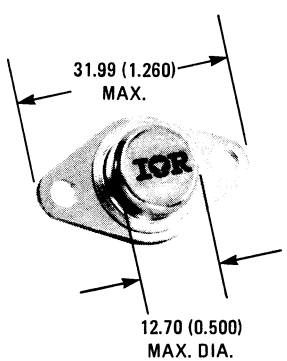
Features:

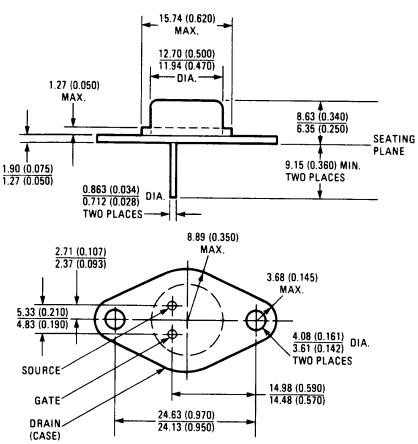
- Fast Switching
- Low Drive Current
- Ease of Paralleling
- No Second Breakdown
- Excellent Temperature Stability

Product Summary

Part Number	V_{DS}	$R_{DS(on)}$	I_D
IRFJ140	100V	0.085Ω	15A
IRFJ141	60V	0.085Ω	15A
IRFJ142	100V	0.11Ω	10A
IRFJ143	60V	0.11Ω	10A

CASE STYLE AND DIMENSIONS





Conforms to JEDEC Case Style TO-213AA (TO-66)
Dimensions in Millimeters and (Inches)

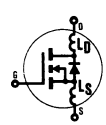
Absolute Maximum Ratings

Parameter		IRFJ140	IRFJ141	IRFJ142	IRFJ143	Units
V_{DS}	Drain - Source Voltage ①	100	60	100	60	V
V_{DGR}	Drain - Gate Voltage (R_{GS} = 20 KΩ) ①	100	60	100	60	V
I_D @ T_C = 25°C	Continuous Drain Current *	15	15	10	10	A
I_D @ T_C = 100°C	Continuous Drain Current *	13	13	8.0	8.0	A
I_{DM}	Pulsed Drain Current ③	60	60	40	40	A
V_{GS}	Gate - Source Voltage	±20				V
P_D @ T_C = 25°C	Max. Power Dissipation	70 (See Fig. 14)				W
	Linear Derating Factor	0.55 (See Fig. 14)				W/K
I_{LM}	Inductive Current, Clamped	(See Fig. 15 and 16) L = 100μH				A
		60	60	40	40	
T_J T_{stg}	Operating Junction and Storage Temperature Range	-55 to 150				°C
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)				°C

Electrical Characteristics @T_C = 25°C (Unless Otherwise Specified)

Parameter		Type	Min.	Typ.	Max.	Units	Test Conditions
BV_{DSS}	Drain - Source Breakdown Voltage	IRFJ140 IRFJ142	100	–	–	V	V_{GS} = 0V
		IRFJ141 IRFJ143	60	–	–	V	I_D = 250μA
$V_{GS(th)}$	Gate Threshold Voltage	ALL	2.0	–	4.0	V	V_{DS} = V_{GS}, I_D = 250μA
I_{GSS}	Gate - Source Leakage Forward	ALL	–	–	100	nA	V_{GS} = 20V
I_{GSS}	Gate - Source Leakage Reverse	ALL	–	–	-100	nA	V_{GS} = -20V
I_{DSS}	Zero Gate Voltage Drain Current	ALL	–	–	250	μA	V_{DS} = Max. Rating, V_{GS} = 0V
			–	–	1000	μA	V_{DS} = Max. Rating x 0.8, V_{GS} = 0V, T_C = 125°C
$I_{D(on)}$	On-State Drain Current ②	IRFJ140 IRFJ141	15	–	–	A	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max.}$, V_{GS} = 10V
		IRFJ142 IRFJ143	10	–	–	A	
$R_{DS(on)}$	Static Drain-Source On-State Resistance ②	IRFJ140 IRFJ141	–	0.07	0.085	Ω	V_{GS} = 10V, I_D = 10A
		IRFJ142 IRFJ143	–	0.09	0.11	Ω	
g_{fs}	Forward Transconductance ②	ALL	6.0	10	–	S (℧)	V_{DS} > $I_{D(on)}$ x $R_{DS(on)max.}$, I_D = 10A
C_{iss}	Input Capacitance	ALL	–	1275	1600	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1.0 MHz See Fig. 10
C_{oss}	Output Capacitance	ALL	–	550	800	pF	
C_{rss}	Reverse Transfer Capacitance	ALL	–	160	300	pF	
$t_{d(on)}$	Turn-On Delay Time	ALL	–	16	30	ns	V_{DD} ≈ 30V, I_D = 10A, Z_o = 4.7Ω See Fig. 17 (MOSFET switching times are essentially independent of operating temperature.)
t_r	Rise Time	ALL	–	27	60	ns	
$t_{d(off)}$	Turn-Off Delay Time	ALL	–	38	80	ns	
t_f	Fall Time	ALL	–	14	30	ns	
Q_g	Total Gate Charge (Gate-Source Plus Gate-Drain)	ALL	–	38	60	nC	V_{GS} = 10V, I_D = 26A, V_{DS} = 0.8 Max. Rating. See Fig. 18 for test circuit. (Gate charge is essentially independent of operating temperature.)
Q_{gs}	Gate-Source Charge	ALL	–	17	–	nC	
Q_{gd}	Gate-Drain ("Miller") Charge	ALL	–	21	–	nC	
L_D	Internal Drain Inductance	ALL	–	5.0	–	nH	Measured between the contact screw on header that is closer to source and gate pins and center of die.
L_S	Internal Source Inductance	ALL	–	12.5	–	nH	Measured from the source pin, 6 mm (0.25 in.) from header and source bonding pad.

Modified MOSFET symbol showing the internal device inductances.



Thermal Resistance

R_{thJC}	Junction-to-Case	ALL	–	–	1.8	K/W	
R_{thCS}	Case-to-Sink	ALL	–	0.2	–	K/W	Mounting surface flat, smooth, and greased.
R_{thJA}	Junction-to-Ambient	ALL	–	–	50	K/W	Free Air Operation

*I_D LIMITED BY PIN DIMENSION

Source-Drain Diode Ratings and Characteristics

I_S	Continuous Source Current (Body Diode)	IRFJ140 IRFJ141	–	–	15	A	Modified MOSFET symbol showing the integral reverse P-N junction rectifier.
		IRFJ142 IRFJ143	–	–	10	A	
I_{SM}	Pulse Source Current (Body Diode) ③	IRFJ140 IRFJ141	–	–	40	A	
		IRFJ142 IRFJ143	–	–	40	A	
V_{SD}	Diode Forward Voltage ②	IRFJ140 IRFJ141	–	–	2.5	V	T_C = 25°C, I_S = 15A, V_{GS} = 0V
		IRFJ142 IRFJ143	–	–	2.3	V	T_C = 25°C, I_S = 15A, V_{GS} = 0V
t_{rr}	Reverse Recovery Time	ALL	–	500	–	ns	T_J = 150°C, I_F = 15A, dI_F/dt = 100A/μs
Q_{RR}	Reverse Recovered Charge	ALL	–	2.9	–	μC	T_J = 150°C, I_F = 15A, dI_F/dt = 100A/μs
t_{on}	Forward Turn-on Time	ALL	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L_S + L_D.				

①T_J = 25°C to 150°C. ②Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 2%. ③Repetitive Rating: Pulse width limited by max. junction temperature. See Transient Thermal Impedance Curve (Fig. 5).

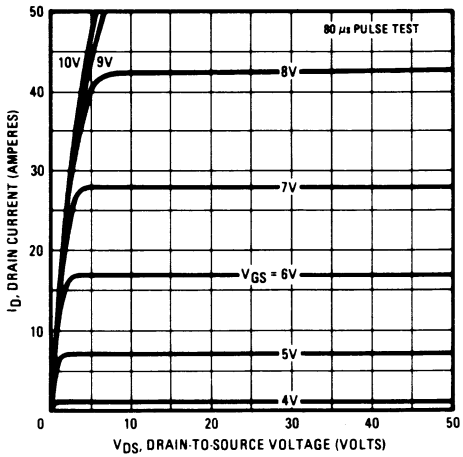


Fig. 1 – Typical Output Characteristics

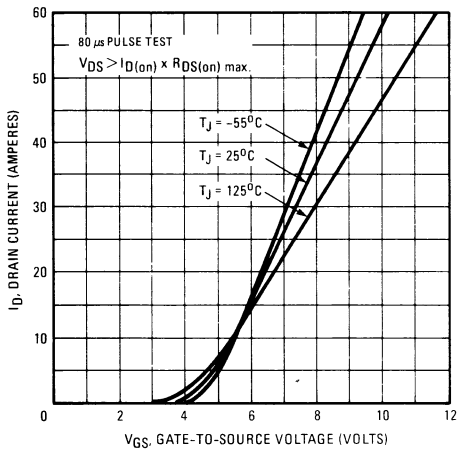


Fig. 2 – Typical Transfer Characteristics

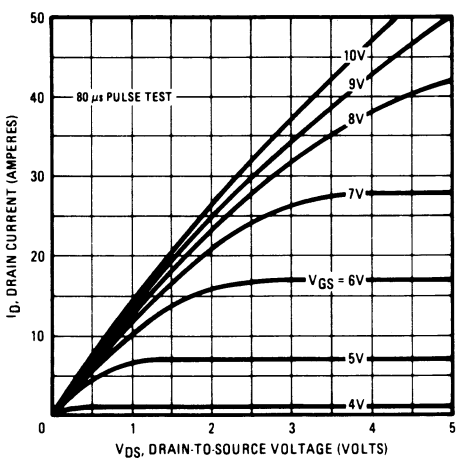


Fig. 3 – Typical Saturation Characteristics

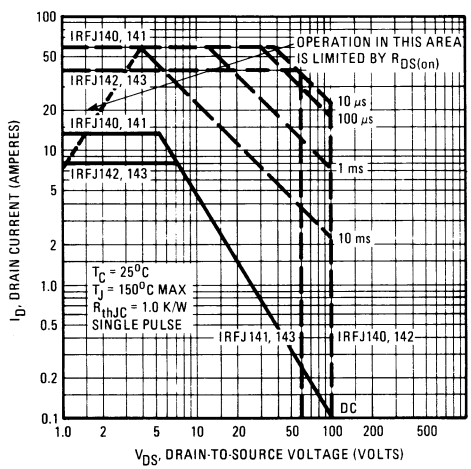


Fig. 4 – Maximum Safe Operating Area

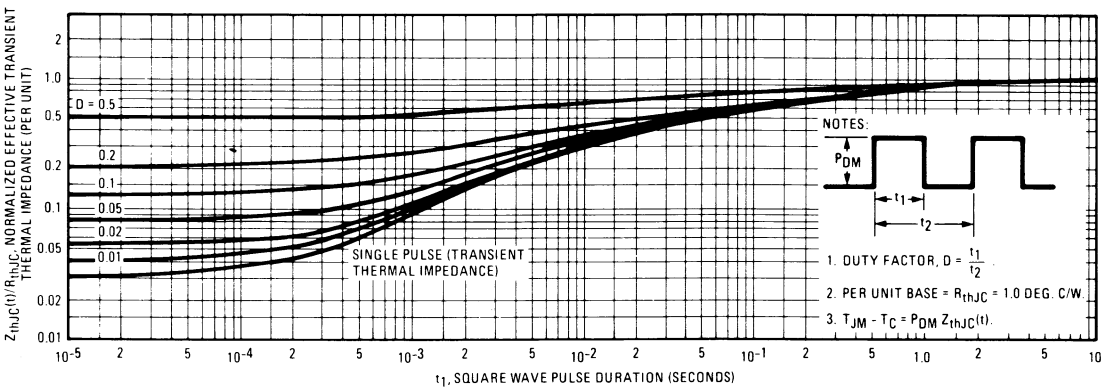


Fig. 5 – Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

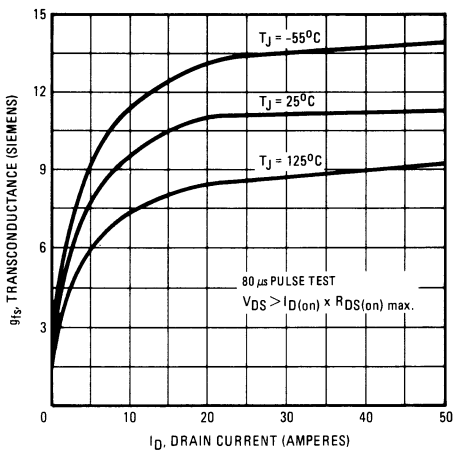


Fig. 6 – Typical Transconductance Vs. Drain Current

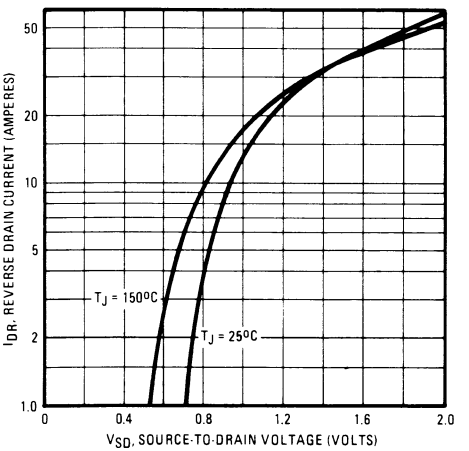


Fig. 7 – Typical Source-Drain Diode Forward Voltage

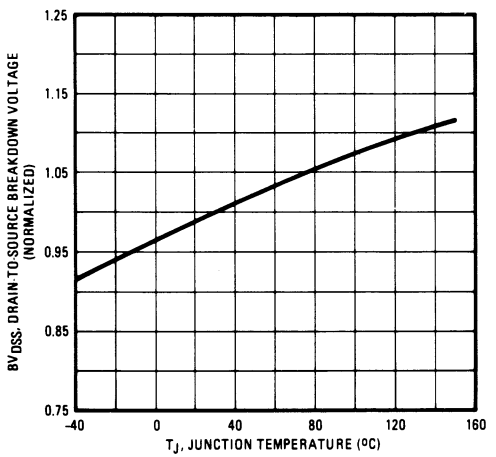


Fig. 8 – Breakdown Voltage Vs. Temperature

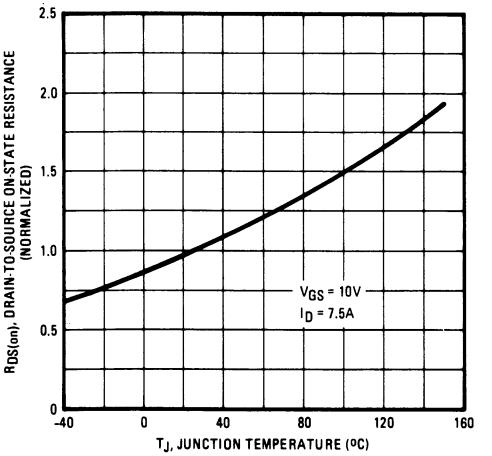


Fig. 9 – Normalized On-Resistance Vs. Temperature

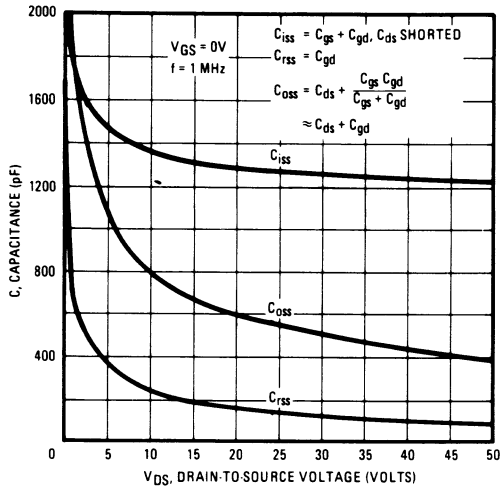


Fig. 10 – Typical Capacitance Vs. Drain-to-Source Voltage

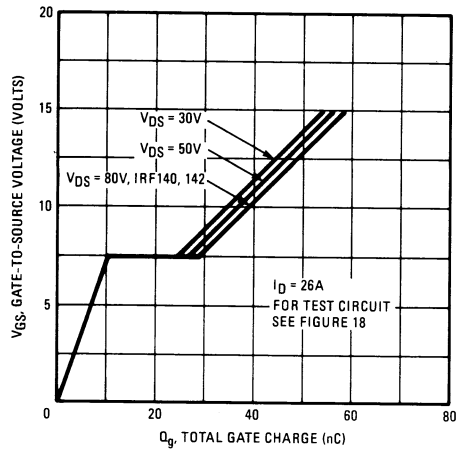


Fig. 11 – Typical Gate Charge Vs. Gate-to-Source Voltage

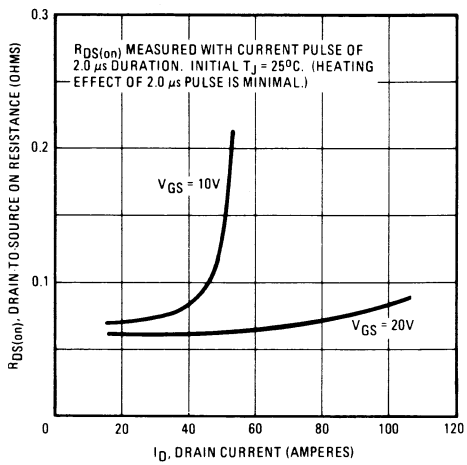


Fig. 12 – Typical On-Resistance Vs. Drain Current

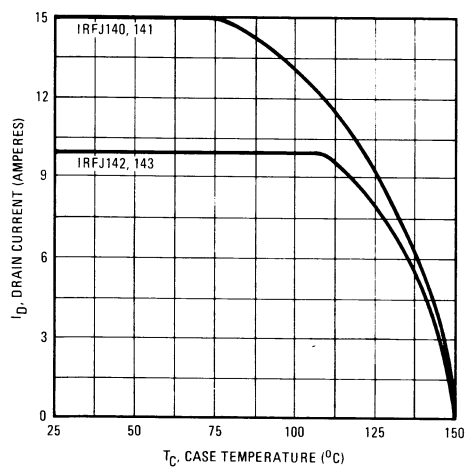


Fig. 13 – Maximum Drain Current Vs. Case Temperature

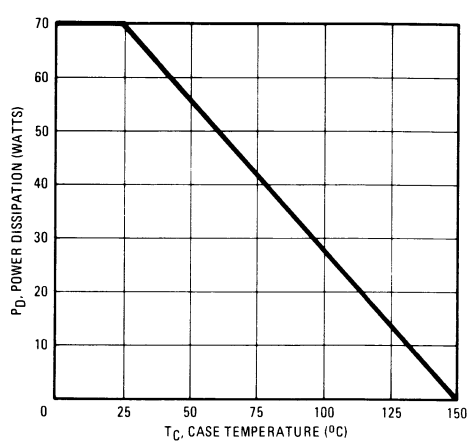


Fig. 14 – Power Vs. Temperature Derating Curve

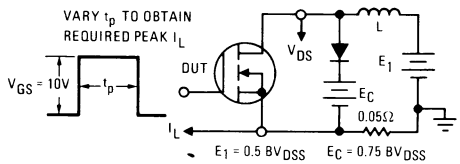


Fig. 15 – Clamped Inductive Test Circuit

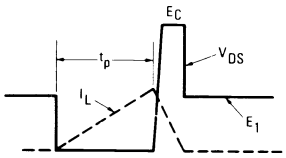


Fig. 16 – Clamped Inductive Waveforms

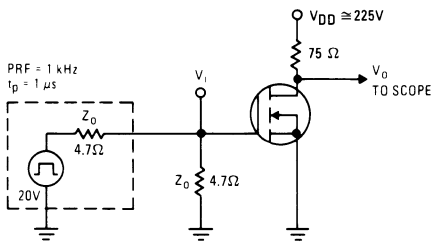


Fig. 17 – Switching Time Test Circuit

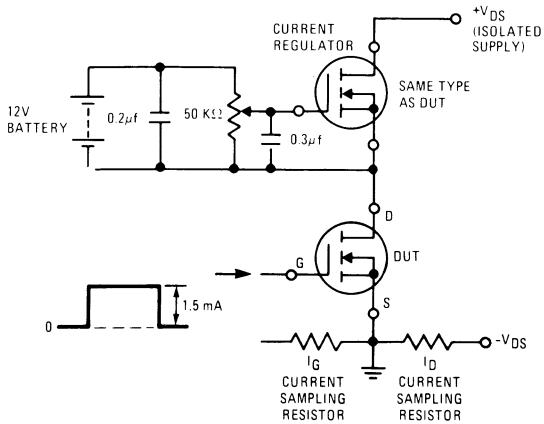


Fig. 18 – Gate Charge Test Circuit

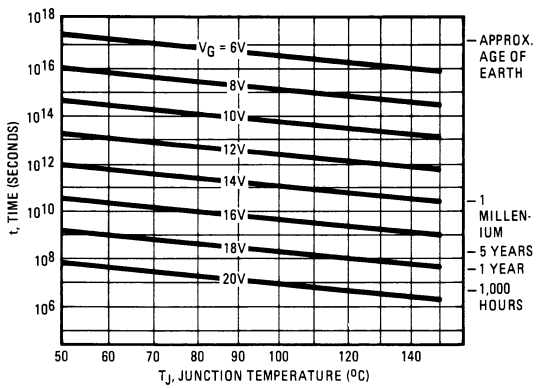


*Fig. 19 – Typical Time to Accumulated 1% Failure

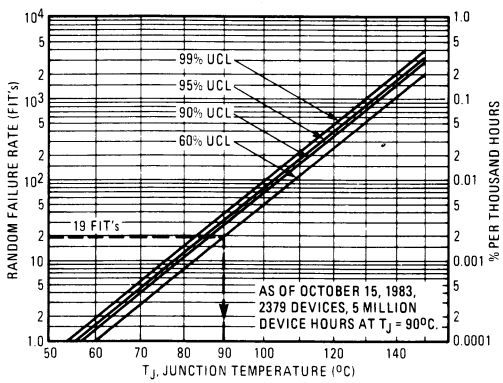


Fig. 20 – Typical High Temperature Reverse Bias (HTRB) Failure Rate

*The data shown is correct as of April 15, 1984. This information is updated on a quarterly basis; for the latest reliability data, please contact your local IR field office.